

Single 2-Input AND Gate

General Description

The ET74AUP1G08N is a single 2-input AND Gate operating from a 0.8V to 3.6V supply. This device is fabricated with advanced CMOS technology to achieve ultra-high speed with high output drive.

Features

- Designed for 0.8V to 3.6V VCC Operation
- Low Static Power Consumption; $I_{CC} = 0.7\mu A$ (Maximum)
- $\pm 4mA$ Balanced Output Sink and Source Capability
- Near Zero Static Supply Current Substantially Reduces System Power Requirements
- These Devices are Pb-Free and RoHS Compliant
- ESD Protection Complies with JESD22 Standard
 - HBM: $\pm 4000V$ Pass (JEDEC JS-001)
 - CDM: $\pm 1000V$ Pass (JEDEC JS-002)
- Latch-up Performance Exceeds $\pm 100mA$ per JEDEC JESD78F
- Part No. and Package Information

Part No.	Package	Packing Option	MSL
ET74AUP1G08N	DFN6 (1.0mm × 1.0mm)	Tape and Reel, 5K/Reel	1

Pin Configuration

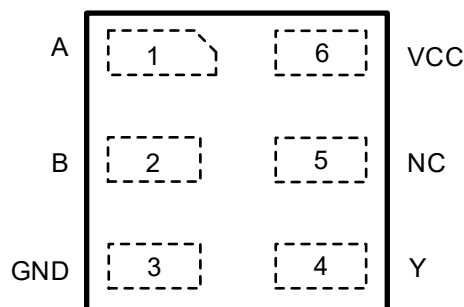


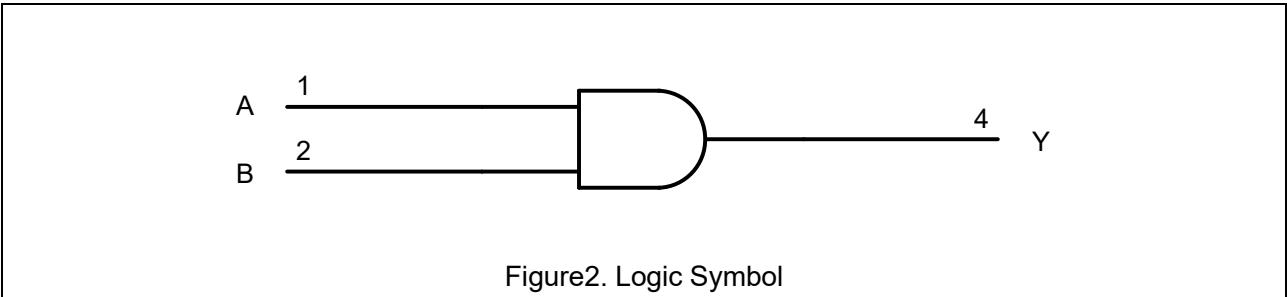
Figure1. Pin Configuration

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Pin Function

Pin No.	Pin Name	Function
1	A	Input A
2	B	Input B
3	GND	Ground
4	Y	Output
5	NC	No Connect
6	VCC	Supply Voltage

Block Diagram



Functional Table

Input		Output
A	B	Y
L	L	L
L	H	L
H	L	L
H	H	H

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Absolute Maximum Ratings

Symbol	Parameter		Value	Unit
V _{CC}	DC Supply Voltage (VCC Pin)		-0.5 to 4.6	V
V _I	DC Input Voltage ⁽¹⁾		-0.5 ≤ V _I ≤ 4.6	V
V _O	DC Output Voltage Output in Higher or Low State		-0.5 to 4.6	V
I _{IK}	DC Input Diode Current, V _I < GND		-50	mA
I _{OK}	DC Output Diode Current, V _O < GND, V _O > V _{CC}		±50	mA
I _O	DC Output Sink Current		±50	mA
I _{CC}	DC Supply Current per Supply Pin		+100	mA
I _{GND}	DC Ground Current per Supply Pin		-100	mA
T _{STG}	Storage Temperature Range		-65 to 150	°C
T _L	Lead Temperature, Soldering 10 Seconds		260	°C
T _J	Max Junction Temperature		150	°C
V _{ESD}	ESD Classification	Human Body Model ⁽²⁾	±4000	V
		Charged Device Model ⁽³⁾	±1000	
I _{LU}	Max Latch Up Current Above V _{CC} and GND at 125°C ⁽⁴⁾		±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

Note1: I_O absolute maximum rating must be observed.

Note2: HBM tested per JEDEC JS-001;

Note3: CDM tested per JEDEC JS-002;

Note4: Latch up Current Maximum Rating tested per JEDEC JESD78F.

Thermal Characteristics

Symbol	Package	Ratings	Value	Unit
R _{θJA}	DFN6	Thermal Characteristics, Thermal Resistance, Junction-to-Air	440	°C/W
R _{θJB}	DFN6	Thermal Characteristics, Thermal Resistance, Junction-to-board	285	°C/W
P _D	DFN6	Power Dissipation in Still Air at 85°C	150	mW

Recommended Operating Conditions

Symbol	Parameter		Min	Max	Unit
V _{CC}	DC Supply Voltage Operating		0.8	3.6	V
V _I	DC Input Voltage		0	V _{CC}	V
V _O	DC Output Voltage (High or Low State)		0	V _{CC}	V
T _A	Operating Temperature Range		-40	125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 0.8V to 3.6V	0	20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied.

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Electrical Characteristics

DC Electrical Characteristics

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
V _{IH}	High-Level Input Voltage		0.8	0.75V _{CC}			0.75V _{CC}		V
			0.9~1.95	0.7V _{CC}			0.7V _{CC}		
			2.3~2.7	1.6			1.6		
			3.0~3.6	2.0			2.0		
V _{IL}	Low-Level Input Voltage		0.8			0.25V _{CC}		0.25V _{CC}	V
			0.9~1.95			0.3V _{CC}		0.3V _{CC}	
			2.3~2.7			0.7		0.7	
			3.0~3.6			0.9		0.9	
V _{OH}	High-Level Output Voltage	I _{OH} = -20uA	0.8~3.6	V _{CC} - 0.1			V _{CC} - 0.1		V
		I _{OH} = -1.1mA	1.1	0.82	1.02		0.77		
		I _{OH} = -1.7mA	1.4	1.11	1.32		1.03		
		I _{OH} = -1.9mA	1.65	1.32	1.58		1.30		
		I _{OH} = -2.3mA	2.3	2.05	2.24		1.97		
		I _{OH} = -3.1mA		1.9	2.22		1.85		
		I _{OH} = -2.7mA	3.0	2.72	2.95		2.67		
		I _{OH} = -4.0mA		2.6	2.92		2.55		
V _{OL}	Low-Level Output Voltage	I _{OL} = 20uA	0.8~3.6			0.1		0.1	V
		I _{OL} = 1.1mA	1.1		0.11	0.33		0.33	
		I _{OL} = 1.7mA	1.4		0.12	0.31		0.37	
		I _{OL} = 1.9mA	1.65		0.11	0.31		0.35	
		I _{OL} = 2.3mA	2.3		0.14	0.31		0.33	
		I _{OL} = 3.1mA			0.19	0.44		0.45	
		I _{OL} = 2.7mA	3.0		0.11	0.31		0.33	
		I _{OL} = 4.0mA			0.16	0.44		0.45	
I _{IN}	Input Leakage Current	V _I = V _{CC} or GND	0~3.6			±0.1		±0.2	uA
I _{OFF}	Power Off Leakage Current	V _I = 3.6V or V _O = 3.6V	0			±0.2		±0.5	uA

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DC Electrical Characteristics

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25 °C			-40°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
ΔI _{OFF}	Additional Power Off Leakage Current	V _I or V _O = 0~3.6V	0~0.2			±0.2		±0.6	uA
I _{CC}	Quiescent Supply Current	V _I = 3.6V or GND	3.6			±0.2		±0.7	uA
Δ I _{CC}	Additional Quiescent Supply Current	V _I = 2.7V	3.3			60		90	uA

AC Electrical Characteristics

t_r = t_f = 3ns

Symbol	Parameter	Condition	V _{CC} (V)	T _A = 25°C			-40°C ≤ T _A ≤ 125°C		Unit
				Min	Typ	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation Delay (Figure3 and 4)	C _L = 5pF ⁽⁵⁾	0.8	13.2	29	90.1	11.9	220	ns
			1.2	5.0	7.6	14.3	4.6	14.4	
			1.5	3.4	4.8	8.9	3	9.6	
			1.8	2.7	3.6	6.9	2.3	7.6	
			2.5	1.9	2.4	5.1	1.6	5.6	
			3.3	1.5	1.9	4.4	1.3	4.8	
		C _L = 10pF ⁽⁵⁾	0.8	14.3	31.3	97.9	12.8	239	ns
			1.2	5.4	8.3	15.3	5.0	15.3	
			1.5	3.7	5.2	9.5	3.2	10.2	
			1.8	2.9	3.9	7.4	2.5	8.1	
			2.5	2.0	2.6	5.4	1.7	6.0	
			3.3	1.6	2.0	4.6	1.3	5.1	
		C _L = 15pF ⁽⁵⁾	0.8	15.3	32.5	106	13.8	259	ns
			1.2	5.8	8.9	16.3	5.3	16.3	
			1.5	4.0	5.6	10.1	3.5	10.9	
			1.8	3.1	4.2	7.8	2.6	8.6	
			2.5	2.1	2.8	5.8	1.8	6.4	
			3.3	1.7	2.2	4.9	1.4	5.4	
		C _L = 30pF ⁽⁵⁾	0.8	18.3	37.5	130	16.6	323	ns
			1.2	7.0	10.7	19.3	6.4	19.3	
			1.5	4.8	6.9	12.0	4.2	12.9	
			1.8	3.7	5.1	9.2	3.2	10.2	
			2.5	2.6	3.5	6.7	2.2	7.5	
			3.3	2.0	2.2	5.6	1.7	6.3	

Note5. C_L includes probe and jig capacitance.

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Capacitance Characteristics

Symbol	Parameter	Condition		Typ	Unit
C _{IN}	Input Capacitance	V _{CC} = 3.6V, V _I = 0V or V _{CC}		2	pF
C _O	Output Capacitance	V _{CC} = 0V, V _O = GND		3	pF
C _{PD}	Power Dissipation Capacitance ⁽⁶⁾	1MHz, V _I = 0V to V _{CC}	V _{CC} = 0.8V	7.6	pF
			V _{CC} = 1.2V	8.1	
			V _{CC} = 1.5V	8.5	
			V _{CC} = 1.8V	8.6	
			V _{CC} = 2.5V	9.0	
			V _{CC} = 3.3V	9.6	

Note6. C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

Σ(C_L × V_{CC}² × f_o) = sum of outputs.

AC Test Circuit

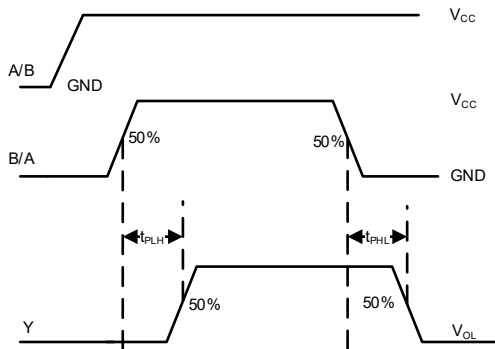


Figure3. Switching Waveform

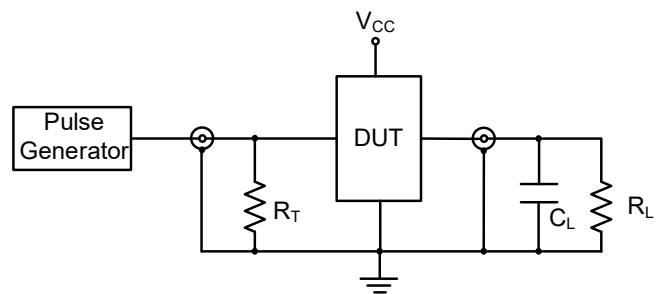
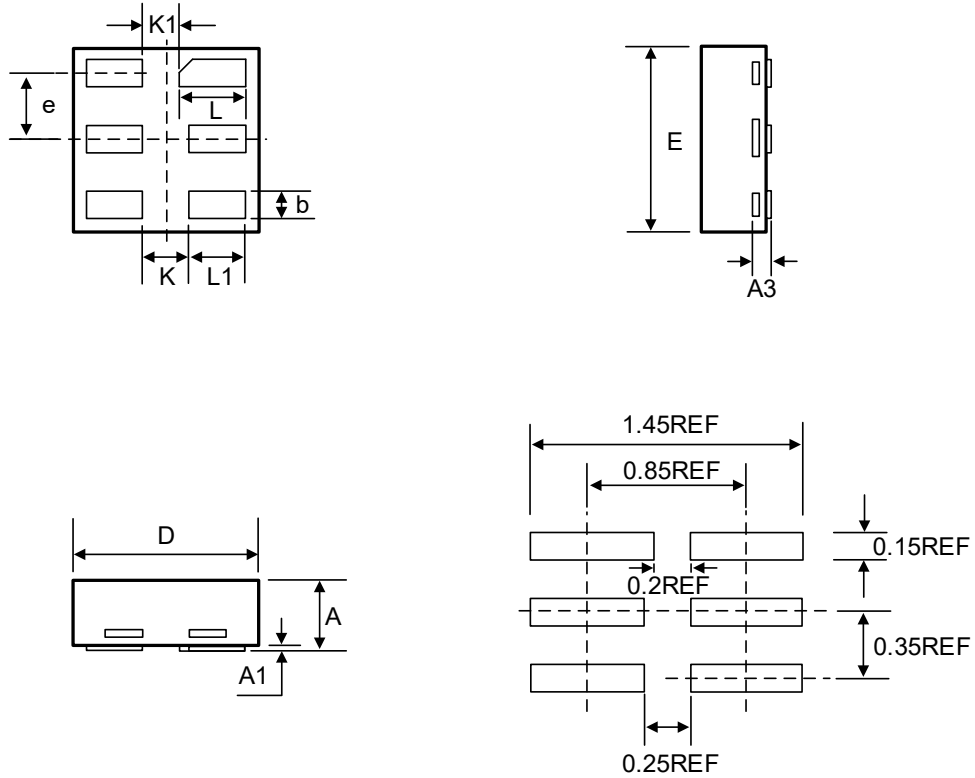


Figure4. Test Circuit

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Package Dimension

DFN6 (1.0mm × 1.0mm)



COMMON DIMENSIONS

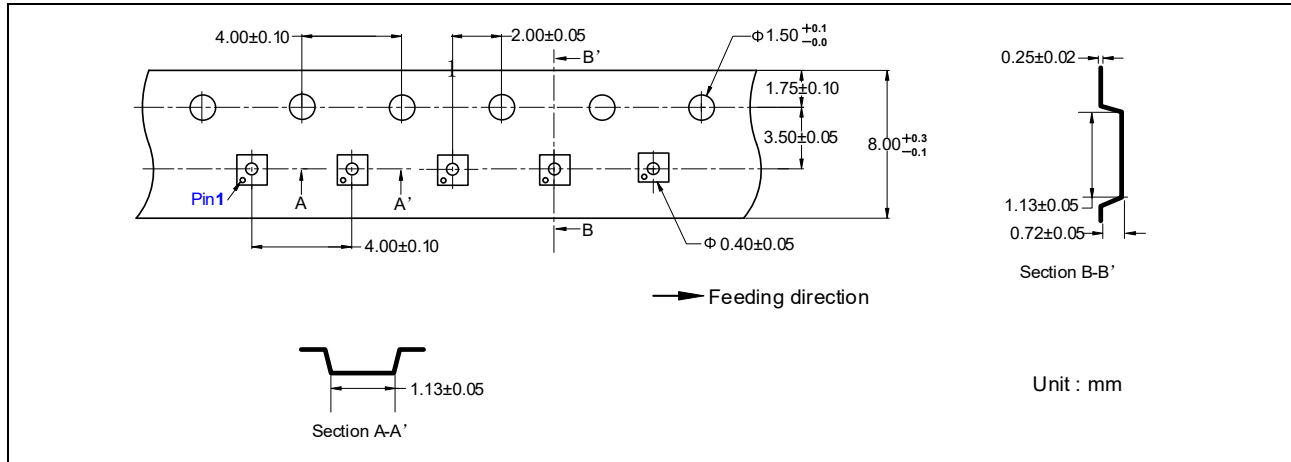
(Unit: mm)

SYMBOL	MIN	NOM	MAX
A	0.50	0.55	0.60
A1	0	0.02	0.05
A3	0.10REF		
b	0.10	0.15	0.20
D	0.95	1.00	1.05
E	0.95	1.00	1.05
e	0.30	0.35	0.40
K	0.25REF		
K1	0.20REF		
L	0.30	0.35	0.40
L1	0.25	0.30	0.35

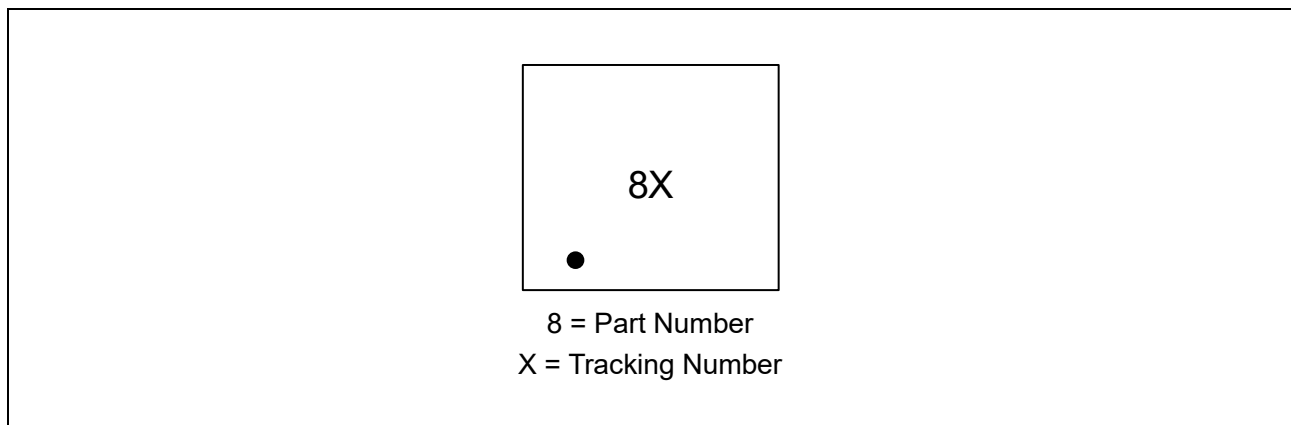
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Tape Information

DFN6(1.0mm × 1.0mm)



Marking Information



Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
1.0	2022-04-18	Initial Version	Shi liangjun	Shi liangjun	Liu jiaying
1.1	2022-09-08	Update Typeset	Shi bo	Shi liangjun	Liu jiaying
1.2	2022-12-4	Update Format and Thermal Characteristics	Wu han	Shi liangjun	Liu jiaying
1.3	2023-11-29	Update ESD/Tape Picture	Shi bo	Shi bo	Liu jiaying
1.4	2025-04-02	Add Marking	Wang peng	Wang peng	Liu jiaying
1.5	2025-05-29	Add Packing Option	Yang xiaoxu	Yang xiaoxu	Liu jiaying
1.5.a	2025-09-02	Update Typeset	Peng junjie	Yang xiaoxu	Liu jiaying
1.5.b	2026-03-09	Update Package Size	Yang xiaoxu	Yang xiaoxu	Liu jiaying